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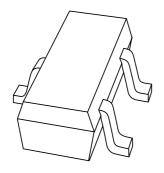
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Kind regards,

Team Nexperia

## **DISCRETE SEMICONDUCTORS**

## DATA SHEET



# BC856T; BC857T series PNP general purpose transistors

Product data sheet Supersedes data of 1999 Apr 26 2000 Nov 15



## PNP general purpose transistors

BC856T; BC857T series

#### **FEATURES**

• Low current (max. 100 mA)

• Low voltage (max. 65 V).

## **APPLICATIONS**

• General purpose switching and amplification, especially in portable equipment.

## **DESCRIPTION**

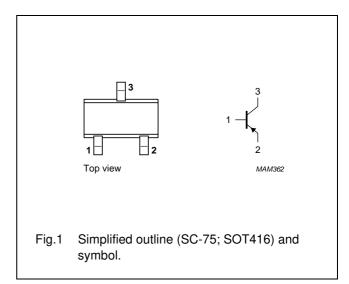
PNP transistor in an SC-75 (SOT416) plastic package. NPN complements: BC846T; BC847T series.

## **MARKING**

TYPE NUMBER	MARKING CODE
BC856AT	3A
BC856BT	3B
BC857AT	3E
BC857BT	3F
BC857CT	3G

#### **PINNING**

PIN	DESCRIPTION
1	base
2	emitter
3	collector



## **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BC856AT; BC856BT		_	-80	V
	BC857AT; BC857BT; BC857CT		_	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	BC856AT; BC856BT		_	-65	V
	BC857AT; BC857BT; BC857CT		_	-45	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	-5	V
I <sub>C</sub>	collector current (DC)		-	-100	mA
I <sub>CM</sub>	peak collector current		-	-200	mA
I <sub>BM</sub>	peak base current		_	-100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	-	150	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

## PNP general purpose transistors

BC856T; BC857T series

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	in free air; note 1	833	K/W

#### Note

1. Transistor mounted on an FR4 printed-circuit board.

## **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -30 \text{ V}; I_E = 0$	_	_	-15	nA
		$V_{CB} = -30 \text{ V}; I_E = 0; T_j = 150 \text{ °C}$	_	_	-5	μΑ
I <sub>EBO</sub>	emitter cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	_	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_C = -2 \text{ mA}$				
	BC856AT; BC857AT		125	_	250	
	BC856BT; BC857BT		220	_	475	
	BC857CT		420	_	800	
V <sub>CEsat</sub>	collector-emitter saturation	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	-	_	-200	mV
	voltage	$I_C = -100 \text{ mA}$ ; $I_B = -5 \text{ mA}$ ; note 1	_	_	-400	mV
$V_{BE}$	base-emitter voltage	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$	-580	_	-700	mV
		$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V}$	-	_	-770	mV
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; f = 1 \text{ MHz}; I_E = i_e = 0$	_	_	2.5	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = -0.5 \text{ V}; f = 1 \text{ MHz}; I_C = I_c = 0$	_	10	_	pF
f <sub>T</sub>	transition frequency	$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V};$ f = 100 MHz	100	_	_	MHz
F	noise figure	$I_{C} = -200 \ \mu A; \ V_{CE} = -5 \ V;$ $R_{S} = 2 \ k\Omega; \ f = 1 \ kHz; \ B = 200 \ Hz$	_	_	10	dB

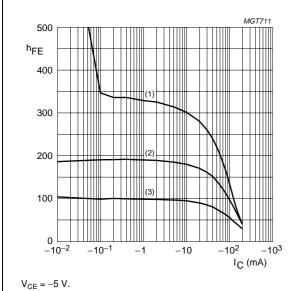
#### Note

1. Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

## PNP general purpose transistors

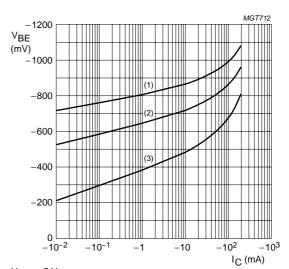
## BC856T; BC857T series

#### **GRAPHICAL INFORMATION BC857AT**



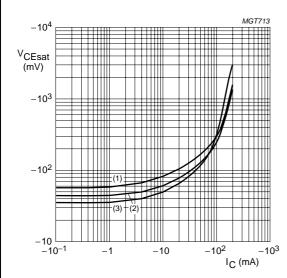
- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.2 DC current gain; typical values.



- $V_{CE} = -5 \text{ V}.$ (1)  $T_{amb} = -55 \text{ }^{\circ}\text{C}.$
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

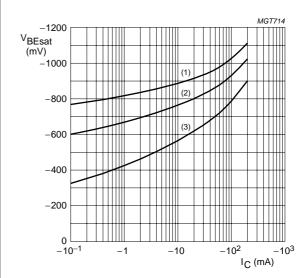
Fig.3 Base-emitter voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20$ .

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20$ .

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

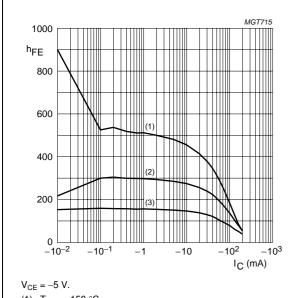
Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

2000 Nov 15 4

## PNP general purpose transistors

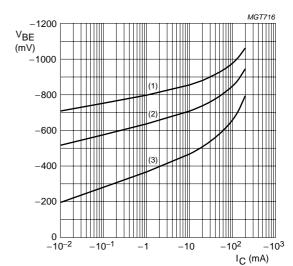
## BC856T; BC857T series

#### **GRAPHICAL INFORMATION BC857BT**



- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

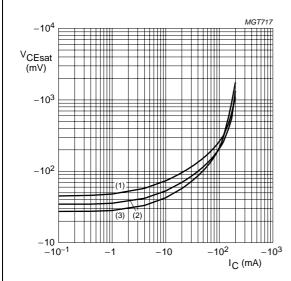
Fig.6 DC current gain; typical values.



 $V_{CE} = -5 \text{ V}.$ 

- (1)  $T_{amb} = -55 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

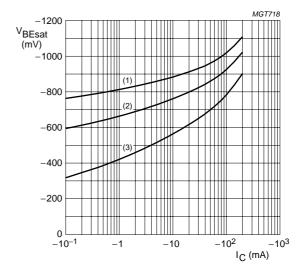
Fig.7 Base-emitter voltage as a function of collector current; typical values.



 $I_{C}/I_{B} = 20.$ 

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.8 Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_{C}/I_{B} = 20.$ 

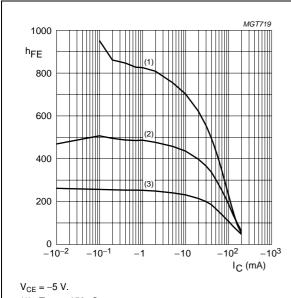
- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.9 Base-emitter saturation voltage as a function of collector current; typical values.

## PNP general purpose transistors

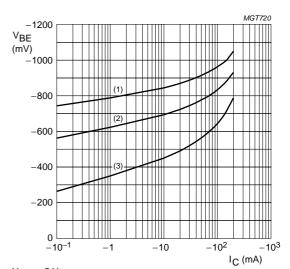
## BC856T; BC857T series

#### **GRAPHICAL INFORMATION BC857CT**



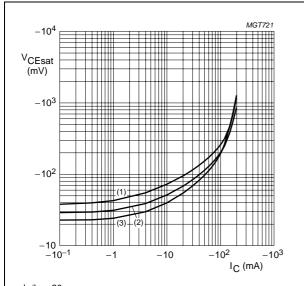
- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.10 DC current gain; typical values.



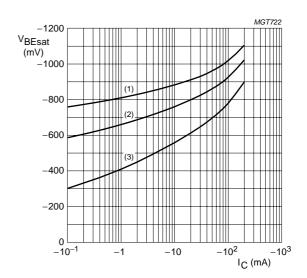
- $V_{CE} = -5 \text{ V}.$
- (1)  $T_{amb} = -55 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.11 Base-emitter voltage as a function of collector current; typical values.



- $I_C/I_B = 20.$
- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.12 Collector-emitter saturation voltage as a function of collector current; typical values.



- $I_{C}/I_{B} = 20.$
- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.13 Base-emitter saturation voltage as a function of collector current; typical values.

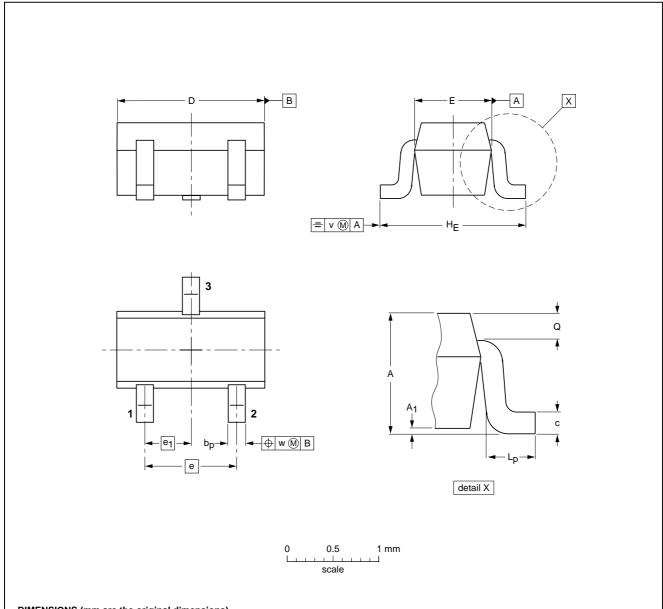
## PNP general purpose transistors

## BC856T; BC857T series

## **PACKAGE OUTLINE**

Plastic surface mounted package; 3 leads

**SOT416** 



## **DIMENSIONS (mm are the original dimensions)**

UNIT	A	A <sub>1</sub> max	bp	С	D	E	е	e <sub>1</sub>	HE	Lp	Q	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE	REFERENCES				EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT416			SC-75			97-02-28

2000 Nov 15 7

## PNP general purpose transistors

BC856T; BC857T series

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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